Failure Analysis Report

TEXAS INSTRUMENTS

TI Information - Selective Disclosure

Device Analysis Services FA QEM-CCR-1706-01197 ACTION-0053471

Customer: Customer Tracking ID: Customer Part ID: Customer Contact: Device Type:	TSMT Johnny.Liang LM4670SD/NOPB	Assy Site: Fab Site: Technology: Analyst: TI Contact: Qty Submitted:	CU6 CUA CMOS Eric Yeh Wendy Huang
Flow Type:	Customer Return	Date Submitted:	2017-06-30
Reviewer:	Owen Ko	Approval:	Owen Ko

Summary				
Failure Analysis	Results			
Customer Reported Failure Mode	 Production line functional test failure. SPK AMP output shorted to GND. 			
TI Failure Description	Pin5 (VO1) shorted to pin4 (GND).			
What effect does the defect or damage cause?	Short failure between fail pin.			
Where and what is the defect/damage?	EOS damage in the form of degraded mold compound was observed.			
Did the identified physical defect/damage explain the TI reported failure mode?	YES.			

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TI	Cust.	Lot Trace	Symbolization	Wafer Fab	Assembly
Unit #	Unit #	Code		Lot #	Lot #
1		5BA0X5U		5001234	5390701EM5

• Customer Reported Problem Description:

1. Production line functional test failure.

2. SPK AMP output shorted to GND.

• TI Problem Description:

Pin5 (VO1) shorted to pin4 (GND).

• Package Analysis:

• External Package Examination:

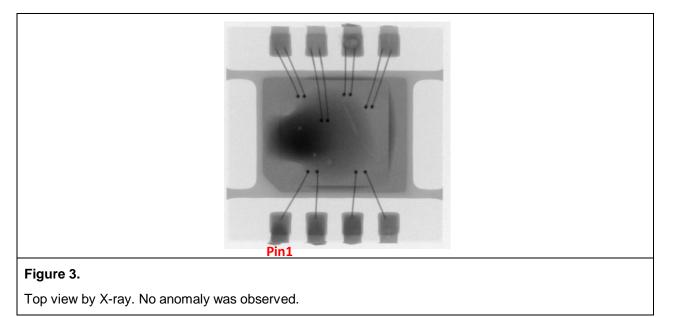
The failing unit was inspected optically. No anomaly was observed.

FBOXS CABZO D	Image: Constraint of the second se		
Figure 1.	Figure 2.		
Optical image of the top of the device.	Optical image of the bottom of the device.		
No anomaly was observed.	No anomaly was observed.		



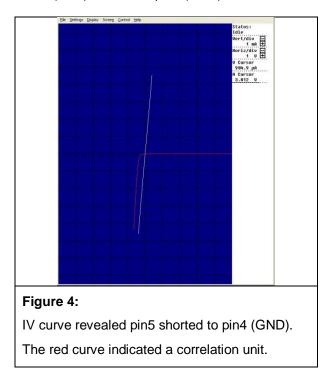
• X-Ray Analysis:

The failing unit was inspected by X-ray. No anomaly was observed.



• Electrical Characterization:

Measurement result for returned unit through curve tracer was as below: Pin5 (VO1) shorted to pin4 (GND).



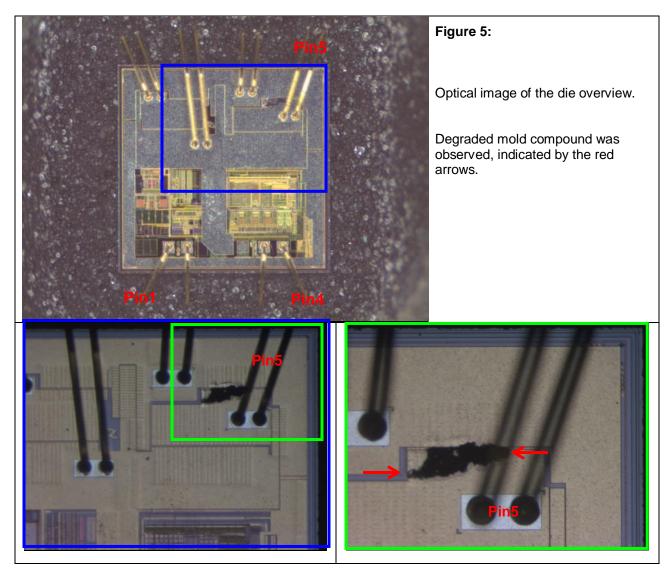


• De-capsulation:

The unit was de-capsulated by laser ablation system followed by mixed acid fuming nitric acid 98%:sulfuric acid 96% = 2:1 on hotplate at 90 degree C.

• Internal Optical Inspection:

Optical inspection of the de-capsulated unit revealed EOS damage in the form of degraded mold compound was observed.



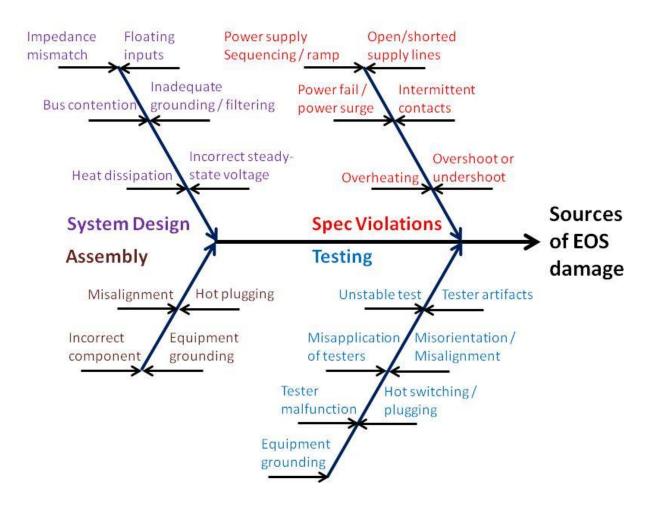


• Physical Mechanism ID:

EOS damage in the form of degraded mold compound was observed.

• Conclusion:

The unit failed due to the EOS damage observed. An over-voltage/over-current condition or event is the most likely cause of failure and we recommend that the customer evaluate the application environment for possible sources of transient or steady-state Electrical Overstress. Detailed analysis and measurement of the customer's board environment and the customer's test environment will be required to identify the specific cause of the EOS. Please consult the below fishbone diagram for a listing of such possible causes.



Note 1: Due to digital image capture, the magnification is not calibrated nor is the aspect ratio maintained. Not all tools provide a means recorded in the image for calibrating the measurements. When a calibration marker is supplied in the image, the measurements may be calibrated in the direction of the marker.